

9. (Previously Amended) A method of manufacturing a semiconductor device, comprising:

creating a semiconductor substrate;

forming an active region over the semiconductor substrate; and

forming an indium doped dielectric layer over at least a portion of the active region, wherein the indium doped dielectric layer has an indium concentration ranging from about 1 mole weight percent to about 15 mole weight percent.

10. (Original) The method as recited in Claim 9 wherein forming an indium doped dielectric layer includes forming an indium doped interlevel dielectric layer.

11. (Original) The method as recited in Claim 9 wherein forming an indium doped dielectric layer includes forming an indium doped silicon dioxide layer.

12. (Original) The method as recited in Claim 9 wherein forming an indium doped dielectric layer includes forming an indium doped dielectric layer to a thickness ranging from about 400 nm to about 1200 nm.

15. (Previously Amended) The method as recited in Claim 9 wherein forming an indium doped dielectric layer includes forming an indium doped dielectric layer using a manufacturing process selected from the group consisting of a physical vapor deposition process or a chemical vapor deposition process.